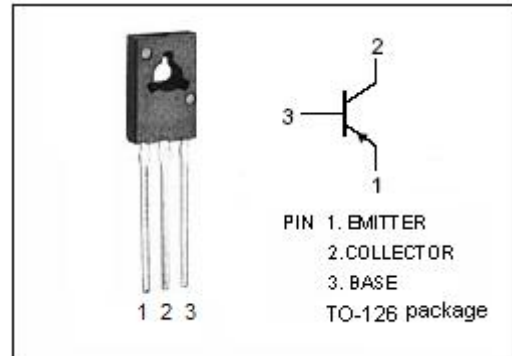


**isc Silicon PNP Power Transistor**
**2SA900**
**DESCRIPTION**

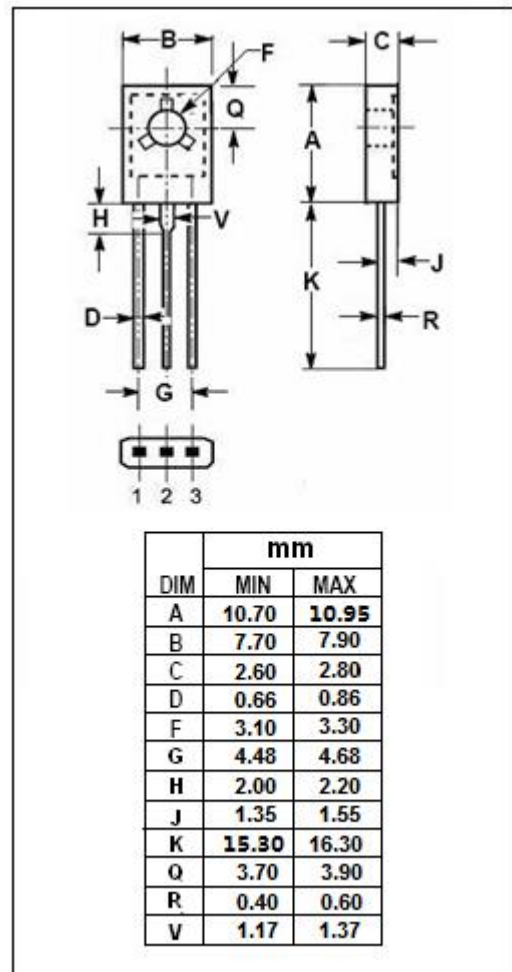
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -18V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Low Collector Saturation Voltage
- Complement to Type 2SC1568
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


**APPLICATIONS**

- Designed for audio frequency power amplifier applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-20	V
$V_{CEO}$	Collector-Emitter Voltage	-18	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_c$	Collector Current-Continuous	-1	A
$I_{CP}$	Collector Current-Pulse	-2	A
$P_C$	Collector Power Dissipation	1.2	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon PNP Power Transistor****2SA900****ELECTRICAL CHARACTERISTICS**T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>B</sub> = 0	-18			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -10 μ A; I <sub>E</sub> = 0	-20			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -10 μ A; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -50mA			-0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -0.5A; I <sub>B</sub> = -50mA			-1.2	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -20V; I <sub>E</sub> = 0			-1	μ A
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -18V; I <sub>B</sub> = 0			-10	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V	90		470	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -1.5A; V <sub>CE</sub> = -2V	50			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -50mA; V <sub>CE</sub> = -6V		200		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = -6V, f <sub>test</sub> = 1MHz		40		pF

◆ **h<sub>FE-1</sub> Classifications**

Q	R	S	T	U
90-155	130-210	180-280	250-360	330-470

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